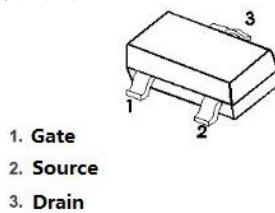


SOT-23

产品特性总结 Product Summary	
VDS	50V
RDS(on)(@VGS= 10V)	<5Ω
RDS(on)(@VGS= 4.5V)	<6Ω

脚位定义 Pin Definition

极限值和温度特性(TA = 25°C 除非另有规定)
Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
漏源电压 Drain-Source Voltage	V _{DS}	100	V
栅源电压 Gate-Source Voltage	V _{GS}	±20	V
漏极连续电流 Continuous Drain Current	I _D	115	mA
漏极脉冲电流 Pulsed Drain Current (note 1)	I _{DM}	460	mA
最大功耗 Maximum Power Dissipation	P _D	0.3	W
结环热阻 Thermal Resistance from Junction to Ambient (note 2)	R _{θJA}	400	°C/W
结温和存储温度 Junction and Storage Temperature	T _J , T _{STG}	-50~+150	°C

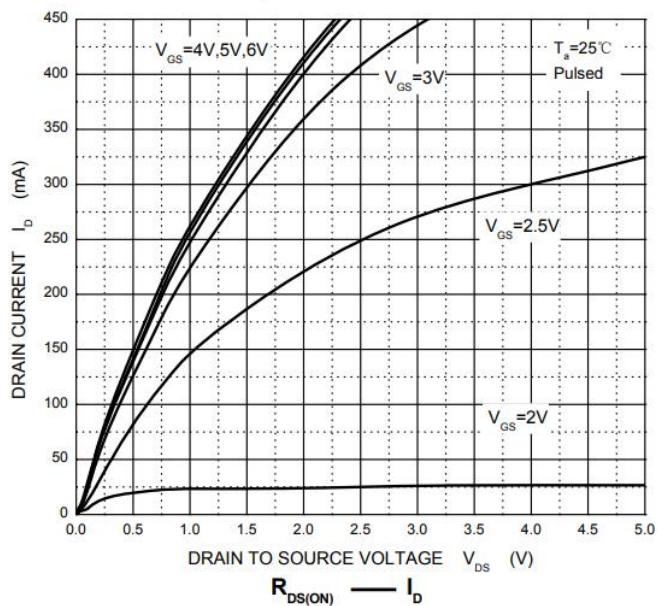
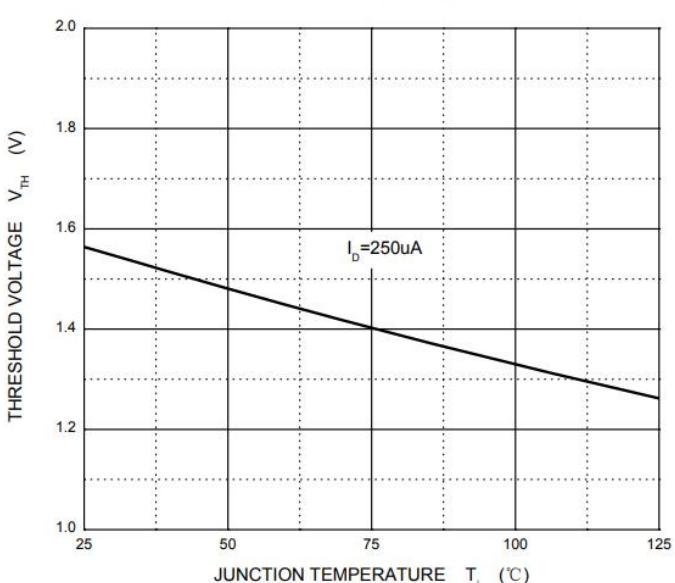
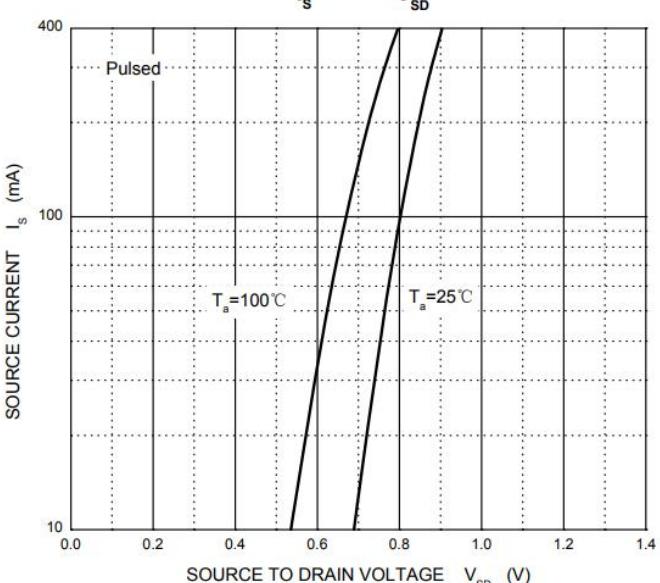
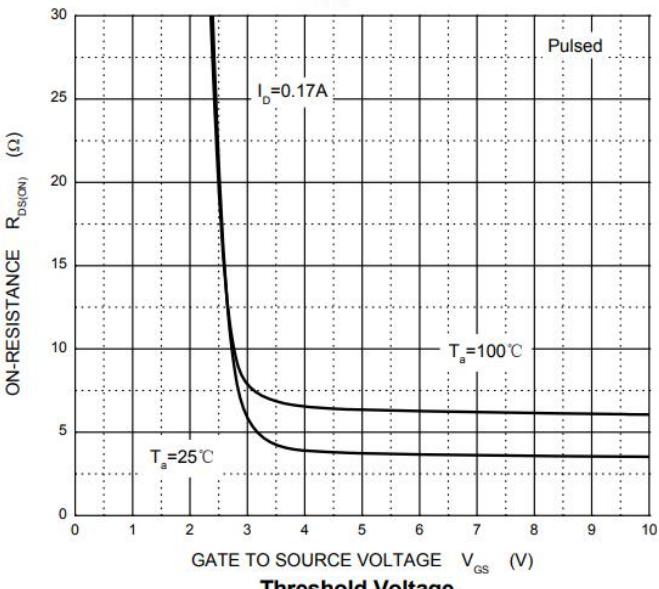
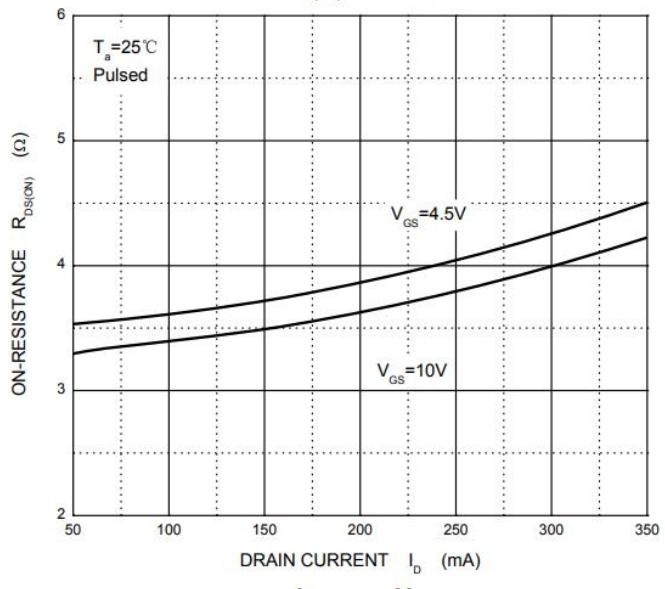
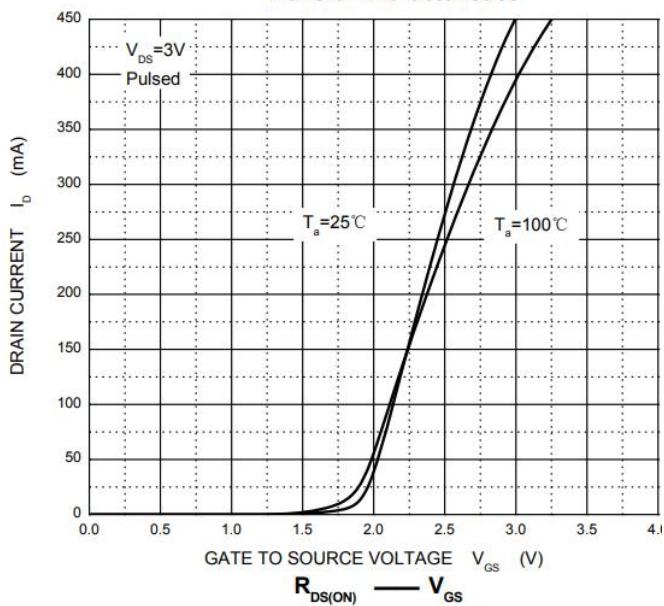
电特性 (TA = 25°C 除非另有规定)
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

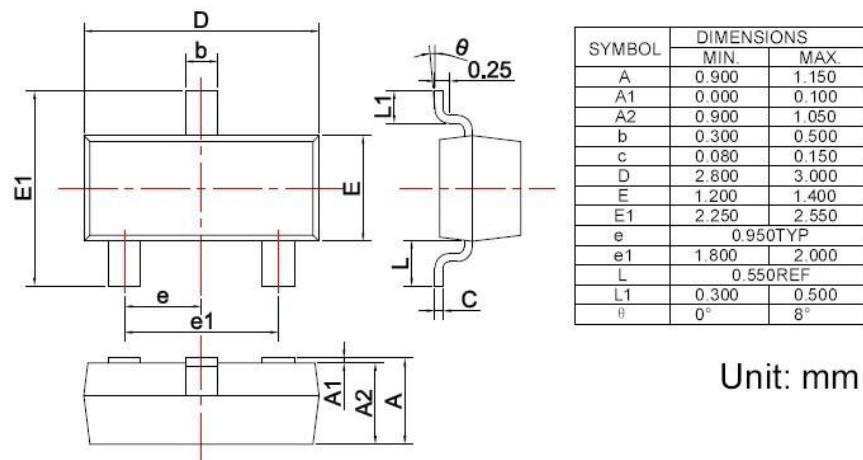
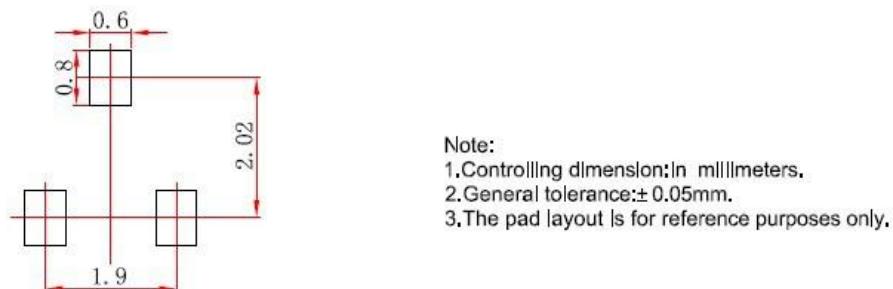
参数 Parameters	符号 Symbol	测试条件 Test Condition	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
静态特性 Static Characteristics						
漏源击穿电压 Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	--	--	V
零栅压漏极电流 Zero gate voltage drain current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V	--	--	1	μA
栅源漏电流 Gate-body leakage current	I _{GSS}	V _{GS} = ± 20V, V _{DS} = 0V	--	--	±10	μA
栅源阈值电压 Gate threshold voltage (note 3)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	2.0	3.0	V
漏源极导通电阻 Drain-source on-resistance (note 3)	R _{D(on)}	V _{GS} = 10V, I _D = 0.12A	--	3.5	5	Ω
		V _{GS} = 4.5V, I _D = 0.1A	--	4	6	Ω
二极管正向电压 Diode forward voltage (note 3)	V _{SD}	I _S = 0.2A, V _{GS} = 0V	--	0.85	1.2	V

动态特性Dynamic Characteristics (note4)						
输入电容Input Capacitance	C _{iss}	V _{DS} = 50V, V _{GS} =0V, f=1MHz	--	31.6	--	pF
输出电容Output Capacitance	C _{oss}		--	1.4	--	pF
反向传输电容 Reverse Transfer Capacitance	C _{rss}		--	1	--	pF
开关特性Switching Characteristics (note 4)						
开启延迟时间Turn-on delay time	t _{d(on)}	V _{DD} = 50V, I _D = 0.2A, R _G = 3.3Ω, V _{GS} = 10V	--	2	--	ns
开启上升沿时间Turn-on rise time	t _r		--	3.1	--	ns
关断延迟时间Turn-off delay time	t _{d(off)}		--	6.5	--	ns
关断下降沿时间Turn-off fall time	t _f		--	15	--	ns
总栅极电荷Total Gate Charge	Q _g	V _{DS} = 50V, I _D =0.2A, V _{GS} =10V	--	0.54	--	nC
栅源电荷Gate-Source Charge	Q _{gs}		--	0.08	--	nC
栅漏电荷Gate-Drain Charge	Q _{gd}		--	0.18	--	nC

***Notes :**

1. Repetitive rating: Pulse width limited by maximum junction temperature
2. Surface Mounted on FR4 board, t≤10 sec.
3. Pulse test : Pulse width≤300μs, duty cycle≤2%.
4. Guaranteed by design, not subject to production.

典型特性曲线 Typical characteristics
Output Characteristics

Transfer Characteristics


封装外形图 SOT-23 Package Outline Dimensions

焊盘设计参考 Precautions: PCB Design


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